# 國立交通大學

電機學院IC設計產業研發碩士班

## 碩士論文

一個 1.25GHz具有高解析度與 8 個相位輸出 之數位控制震盪器,應用於全數位鎖相迴路 A 1.25GHz digitally controlled oscillator with high-resolution and 8-phase output for ADPLL

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# 一個 1.25GHz具有高解析度與 8 個相位輸出 之數位控制震盪器,應用於全數位鎖相迴路

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## 摘要

現代的系統單晶片(SoC)需要晶片內在的時脈產生器以及產生許多不同的頻率,來提供給其他子系統使用,一般常用鎖相迴路為基礎的時脈產生器來達成此任務;然而,鎖相迴路參數為了減少抖動量以及保持迴路的穩定度,因而必須依照輸出頻率以及頻率產生倍數來調整,現有之類比電路方式需要較長的設計週期。

本論文中,為了大幅降低高速傳輸之接收器硬體銷耗及設計的難度,提出了一個可操作在高振盪頻率(Giga Hz)、高解析度、多重相位(8 個相位)輸出之數位控制振盪器電路(DCO),此 DCO 將應用於"8-phase output 之 1.25GHz 的 ADPLL",而此 ADPLL 再將應用於具有"2.5Gb/s 之 data-transceiver"。為了減少鎖相迴路之抖動量,所以,提出在數位控制振盪器中利用傳輸閘的寄生電容差值,作為數位控制之延遲單元,藉此提高數位控制振盪器電路之時間解析度。在微調上時間解析度能夠依照使用驅動細胞單元的能力及數位控制之延遲單元的電容差異,作不同的選擇,相對於使用 OAI-AOI 細胞單元或三態緩衝器矩陣,具有較線性的時間解析度。

所提出的電路架構將被實現在 TSMC  $0.18 \mu$  m 1P6M CMOS 製程,晶片面積為 $310 \mu$ m× $220 \mu$ m (不包含 PAD),其操作頻率範圍為 1.06GHz 到 1.50GHz,平均的時間解析度為 0.38ps,當振盪頻率為 1.25GHz,其功率消耗為 34.1mW。

#### 索引詞彙--高時間解析度,數位控制振盪器,全數位鎖相迴路

# A 1.25GHz digitally controlled oscillator with high-resolution and 8-phase output for ADPLL

Student: Yung-Hsiang Yang Advisor: ChauChin Su

## Industrial Technology R & D Master Program of Electrical and Computer Engineering College National Chiao Tung University **Abstract**

Modern system-on-a-chip(SoC) processors often require on-chip clock generation and multiplication to produce several unrelated frequencies for other sub-systems. The PLL-based clock generator is a common way of frequency multiplication to accomplish the task. However, the loop parameters must be adjusted to minimize jitter performance and insure stability for each output frequency and multiplication factors. Conventional analog skills suffer from long design cycle.

In order to reduce the hardware overhead and the design complexity of high speed transceiver, the proposed digitally controlled oscillator has high operation frequency (GHz), high timing resolution, and multi-phase output (8-phase). The proposed DCO can be applied to "a 1.25GHz ADPLL with 8-phase output" and "a 2.5Gb/s data-transceiver architecture". In order to reduce jitter of PLL, therefore, we propose the digitally controlled oscillator (DCO) with novel digital controlled delay cell based on parasitic capacitance difference of transmission gates. This method can enhance the timing resolution of the digitally controlled oscillator (DCO). The timing resolution in fine-tuned stage can be decided from different driving cells and capacitance difference of each digital controlled delay cell. Thus, a high resolution DCO with better timing linearity as compared with OAI-AOI cell or tri-state inverter matrix is achieved.

The proposed digitally controlled oscillator circuit is designed using TSMC 0.18  $\mu$  m 1P6M CMOS process with active die area of  $310\mu m \times 220\mu m$ . The operation frequency range is 1.06GHz to 1.50GHz. Average timing resolution is 0.38ps. The total power consumption of the proposed DCO is 34.1mW when oscillate frequency is 1.25GHz.

Index Terms -high timing resolution, digitally controlled oscillator, ADPLL.

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在這個時候最適合靜下心來,回想這些日子來,所歷經的人、事、物;在就學及離開工作崗位之前,由於有公司主管的鼓勵及體諒,讓我能很順利來這求得新知,並且在我離開公司之際,還默默的幫我跟公司爭取到一些福利,那正像是寒冬裡暖暖的陽光。

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# **Table of Contents**

Chapter 1	Introduction	1
1.1 Moti	vation	1
1.2 Thes	is Organization	3
Chapter 2	Overview of Clock Generators with Phase Locked Loop	p4
2.1 Intro	duction	4
2.2 PLL	Basics	5
2.3 Sum	mary	14
Chapter 3	Clock Generation Circuits Classification	15
3.1 Intro	duction	15
3.2 The A	Analog Clock Generators	15
3.3 The 1	Digital Clock Generators	16
3.4 Anal	ysis of the DCO Category	17
3.5 Sum	mary	23
Chapter 4	Digitally Controlled Oscillator with High Resolution an	ıd
8-Phase Ou	ductionduction	24
4.1 Intro	duction	24
	Concepts of Digitally Controlled Oscillators	
4.3 The 1	Proposed Fine Tune Delay Cell with High Resolution	31
4.4 Struc	eture of the Proposed DCO	36
4.5 Simu	lation Results and Layout	41
4.6 Com	parisons and Summary	46
Chapter 5	Conclusions	47
5.1 Cond	elusions	47
Bibliograph	V	49

# **Lists of Figures**

Figure 1.1 Data transceiver and PLL circuit block	3
Figure 2.1 Block diagram of an analog PLL	5
Figure 2.2 Simple implementation of a first order loop filter	6
Figure 2.3 Magnitude response Second order loop transfer function	7
Figure 2.4 Three state phase frequency detector and PFD state diagram	7
Figure 2.5 Block diagram of a digital PLL with digital block	9
Figure 2.6 Block diagram of an all digital PLL	9
Figure 2.7 ADPLL with fixed high speed clock to form the DCO	10
Figure 2.8 ADPLL with direct DCO synthesis clock	11
Figure 2.9 Function block of ADPLL	12
Figure 3.1 A simple ring oscillator	16
Figure 3.2 All digital ring oscillator	16
Figure 3.3 Ring oscillator frequency vs. ring delay	17
Figure 3.4 A typical ring-oscillator	17
Figure 3.5 Modified architecture	17
Figure 3.6 An improved DCO architecture	19
Figure 3.7 Structure of the cell-based DCO	19
Figure 3.8 DCO using parallel tri-state inverters to adjust frequency	20
Figure 3.9 8-cell DCO with control bit	21
Figure 3.10 Structure of DCO in [16]	21
Figure 3.11 An improved DCO architecture	22
Figure 4.1 The DCO constructed with the DAC and the VCO	26
Figure 4.2 The DCO constructed with the DAC and the VCO in [23]	26
Figure 4.3 The DCO constructed with high speed clock and divider	27
Figure 4.4 The DCO constructed with variable length ring oscillator	27
Figure 4.5 General mechanism for enhance of fine tune in the DCO	28
Figure 4.6 The mechanism are to adjust the resistance	28
Figure 4.7 The mechanism are to adjust the capacitance	29
Figure 4.8 a multiplexer and two identical buffers structure	30
Figure 4.9 replace the multiplexers and the buffers by NAND gates	30
Figure 4.10 a bank of tri-state buffers	30

Figure 4.11 High resolution delay cell	31
Figure 4.12 Conventional control mechanism with shunt capacitor	32
Figure 4.13 Proposed delay cell with transmission gate	33
Figure 4.14 The gate capacitance of transmission gate	34
Figure 4.15 High resolution delay cell	35
Figure 4.16 High resolution delay cell simulation result	35
Figure 4.17 The proposed DCO architecture	37
Figure 4.18 The proposed DCO-cell architecture	37
Figure 4.19 The trigger circuit of the DCO	37
Figure 4.20 The small-signal model of the DCO-cell	38
Figure 4.21 The parameter of the DCO-cell	38
Figure 4.22 Influence of PVT variations on the controllable frequency range	41
Figure 4.23 The clock period range of the DCO at three different corner cases	42
Figure 4.24 Tuning range of medium stage	42
Figure 4.25 Tuning range of fine stage	43
Figure 4.26 The coarse-code vs. medium-code period overlap diagram	43
Figure 4.27 The layout of the proposed digitally controlled oscillator	45

# **Lists of Tables**

Table 2-1 Phase Lock Loop comparison	14
Table 3-1 Characteristics of various clock generation circuits	23
Table 4-1 The form of period overlap	44
Table 4-2 The summary of the performance	45
Table 4-3 Comparison with existing DCOs	46



# Chapter 1

## Introduction



## 1.1 Motivation

Traditionally, phase locked loop based clock generators for microprocessor are the common way of frequency multiplication from a low frequency reference clock, typically from quartz oscillator. As VLSI technology grows up rapidly, the advance of semiconductor process enable the successful realization of system-on-a-chip (SoC). Modern SoC processors integrate both analog and digital real-time functions. An off-chip clock costs power to generate and to distribute on the PC-board. In addition, the ability to oscillate at different frequencies reduces costs by eliminating the need for additional oscillators to a system. Such applications often require on-chip clock generation and multiplication to produce several unrelated frequencies for digital signal processing, I/O interfaces, as well as sampled analog sub-systems [1].

One solution is to create one PLL-based clock generator running at a high frequency that can then be divided down to obtain all the desired frequencies [2]. The disadvantage of this approach is the high power consumption and stringent jitter requirements. Another approach is to have a dedicated PLL for each clock domain.

This solution is very costly in term of power and area.

In addition, most PLL design use mixed signal and full custom design techniques, which can not be fully integrated in digital environment. Due to time-to-market issue, the design cycle remains the same or even shorter. Thus in System-on-a-Chip (SoC) designs [3], each module had better to be reusable and process portable, so that the total design time can be reduced. As a result, how to design a synthesizer clock generator in an efficient way becomes more important.

The all digital PLL have several advantages over their analog counterparts. Firstly, traditional analog loop filter costs a lot of chip area. Using digital loop filters gives benefits such as robustness against noise, and also the ability to design higher order filters without much extra power consumption and areas penalty. Secondly, analog component are vulnerable to DC offset and drift phenomena that are not present in equivalent digital implementations [4].

In order to avoid the disadvantages of analog circuits, an *All Digital Phase-Locked Loop* (ADPLL) has been developed because it has better programmability, stability, and portability over different processes. It can reduce the system turn around time. The ADPLL has some unique advantages such as high noise immunity, short turnaround time, low power consumption, etc. And, this cell-based approach is also suitable for automatic synthesis of ADPLL.

However, due to the limitations of cell-based design, it is difficult to achieve a low-jitter, low-power, and high resolution all-digital cell-based clock generator. So, how to overcome the limitations of standard cells to build a high resolution delay cell with better linearity and less power consumption for DCO are the challenges for our research.

In order to reduce the hardware overhead and the design complexity of high speed transceiver (Figure 1.1), the proposed digitally controlled oscillator has high operation frequency (GHz), high timing resolution, and multi-phase output (8-phase). The proposed DCO can be applied to "a 1.25GHz ADPLL with 8-phase output" and "a 2.5Gb/s data-transceiver architecture", as shown in Figure 1.1. The DCO is consisted of four delay elements with differential operation frequency and 8-phase output. In this thesis, a systematic design method for the DCO design is also presented. As a result, the design methodology proposed can reduce design time and design complexity of the DCO, making it very suitable for SOC applications.

#### 2.5Gb/s Transceiver Architecture

#### 8-phase 1.25GHz ADPLL

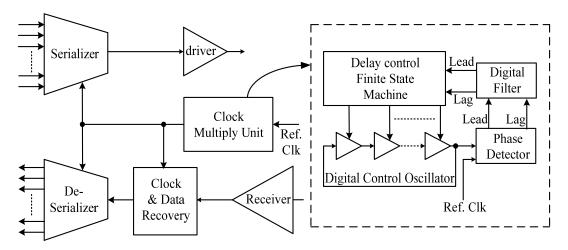


Figure 1.1 Data transceiver and PLL circuit block

## 1.2 Thesis Organization

This thesis is organized into five chapters. In Chapter 1, we introduce that different clock domains are required in a SoC chip. This motivation and design targets of the DCO are explained.

In Chapter 2, we explain an overview of PLL related techniques for clock generator. Properties of analog, digital PLL as well as charge-pump PLL are addressed. Then, all-digital PLL with different DCO approaches are discussed. The design trade-off of clock generator with different PLL architecture is also investigated.

In Chapter 3, we explain an overview of some existing DCO structure. This chapter explains the most important features of conventional clock generators. As highlighted in the abstract, the focus of this thesis is on the digital clock generation method. Analog clock generators are thus only mentioned, and not explained in detail.

In Chapter 4, we first introduce the fundamental of digitally controlled oscillator. This chapter also introduces different approaches to enhance the fine tune solution of the DCO. Then, the chapter explains the operation of digitally controlled delay cells with transmission gates design. And, we apply the digitally controlled delay cell to build high resolution digitally controlled oscillator. Then, we propose a novel digitally controlled oscillator structure. A detailed description of the circuits and experimental results are given.

In Chapter 5, the conclusions of this work are summarized. All the simulation results are also summarized in this chapter.

# Chapter 2

## **Overview of Clock Generators with**

## **Phase Locked Loop**



## 2.1 Introduction

Several methods exist for realizing frequency multiplication: phase locked loops (PLL)[5,6], delay locked loops (DLL)[7], and direct digital synthesis (DDS) in [8]. The basic concept of the DLL is similar to PLL. The major difference is the voltage controlled delay line (VCDL) in the DLL and the voltage controlled oscillator (VCO) in the PLL [9]. Each of these methods has advantages and disadvantages for frequency multiplication. DLL approaches may offer better jitter performance than PLL approaches, because the noise induced by the power supply or substrate noise disappears at the end of the delay line. However, DLL based methods are not suitable for wide multiplication range applications. The direct digital synthesis (DDS) in [8] applied accumulator and D/A converter mechanism for the frequency synthesis. Therefore, we only focus on the PLL approach in this work.

The organization of this chapter is as follows. Section 2.2 describes the preliminary knowledge of analog and digital PLLs, basics of all digital PLL and digitally controlled oscillators applications. Design trade off in different PLL

architecture is discussed in section 2.3.

## 2.2 PLL Basics

PLL based clock generator has been widely used in the industry. The operation principle is summarized in this section and the steps towards digital PLL are described in the subsequent sections.

### **Analog PLL**

The PLL characteristics are determined by the characteristics of phase detector, voltage controlled oscillator and low pass filter. [5,6] indicated two factors that influence the performance. One is the phase error – the difference between the input and output phases. Another is the frequency range – the range over which it will acquire lock. As a result, PLL can be regarded as a tracking phase system. An analog PLL consist of the three main building block as show in Figure 2.1

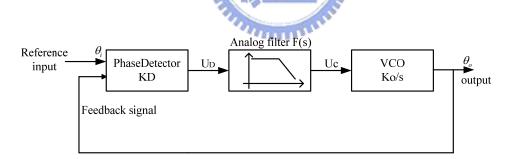


Figure 2.1 Block diagram of an analog PLL.

• **Phase detector:** It compares the phase of the input signal (reference signal) with the phase of the feedback signal. The output of the PD is ideally proportional to the phase difference  $\theta_e$ .

$$U_d(s) = K_d(\theta_i(s) - \theta_o(s)) = K_d\theta_e(s)$$

where  $K_d$  is the PD gain in [V/rad],  $\theta_i$  and  $\theta_o$  are the phase of the input and output signals respectively.

• Low pass filter: The low pass filters the output voltage of the phase detector

with the transfer function F(s).

$$U_c(s) = U_d(s) \cdot F(s)$$

Voltage controlled oscillator: The VCO translates the filter output into a frequency. Due to the transformation of the phase information into a frequency, it has the characteristic of an integrator with gain K<sub>o</sub> [rad/sV].

$$\theta_O = \frac{U_C(s) \cdot K_O}{S}$$

The transfer function of the closed loop becomes the

$$H(s) = \frac{\theta_O(s)}{\theta_i(s)} = \frac{KF(s)}{S + KF(s)} \text{ with } K = K_d K_O$$

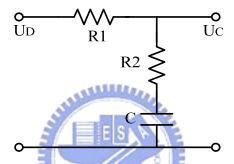


Figure 2.2 Simple implementation of a first order loop filter.

A first order loop filter as depicted in Figure 2.2. It has the following transfer function:

$$F(s) = \frac{1 + SR_2C}{1 + S(R_1C + R_2C)}$$

So, the overall loop transfer function is a second order loop with a low pass characteristic. The natural frequency is

$$\omega_n = \sqrt{\frac{K_D K_O}{R_1 C + R_2 C}}$$

and the damping factor becomes

$$\zeta = \frac{\omega_n}{2} (R_2 C + \frac{1}{K_D K_O})$$

A PLL uses a first order loop filter is therefore a second order system. Figure 2.3 shows the transfer functions of a second order loop for various damping factors  $\zeta$ .

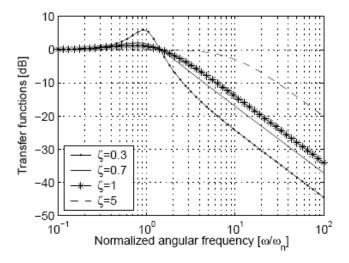


Figure 2.3 Magnitude response Second order loop transfer function.

## **Digital PLL**

The digital phase locked loops differ form their analog counterparts in that input, output, and feedback signals are digital. The phase frequency detector (PFD) is a popular replacement for analog phase detectors. It consists of a state machine with three states ('low', 'zero', 'high'). As illustrated in Figure 2.4, the transitions between the states are triggered by the rising edges of the reference input ('Ref') and feedback signal ('Fb'). If it the PLL is Locked, the states 'low' and 'high' are activated only during extremely short time spans. During the phase locking process the relative time that the state machine remain in 'low' or 'high' state represents the phase error [10].

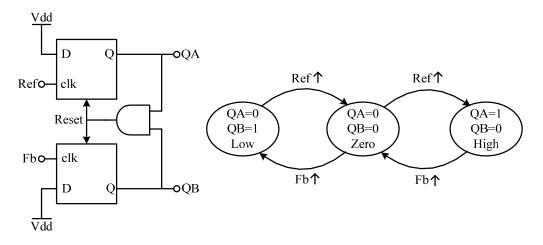


Figure 2.4 Three state phase frequency detector and PFD state diagram.

The PFD stores the order of arrival of the reference and feedback edges. Prior to

phase locking, the frequency of the VCO must be locked. During this phase, the PFD produces an output signal corresponding to the frequency error. Incorrect locking on an integer multiple of the desired VCO frequency is therefore not possible. The outputs of the PFD are usually combined to control a tri-state butter that remains in high-impedance during state 'zero' and outputs logic '1' and '0' in the states 'high' and 'low' respectively. This signal is then directly passed to an analog loop filter that controls the VCO. The phase detector's gain  $K_d$  depend on the output voltage levels of the tri-state buffers [10]:

$$K_d = \frac{U_{high} - U_{low}}{4\pi}$$

With the binary clock in digital signals, usage of frequency dividers is simple. In fact, most digital PLL contain a frequency divider in the feedback path. It allows to generate VCO output frequencies that are an integer multiple of the reference input frequency. The division ratio N has an impact on the overall PLL gain.

$$\theta_{fb}(s) = \frac{\theta_o(s)}{N}$$

$$K = \frac{K_d K_o}{N}$$

When the PLL has locked, the output of the PFD is permanently on high impedance, thus no current is flowing to the loop filter. The charge on the loop filter capacitance is kept constant (beside leakage effects) unit the PFD output is activated. The loop filter depicted in Figure 2.2 works thus as an integrator. The loop filter's transfer function can then be approximated with

$$F(s) = \frac{1 + SR_2C}{S(R_1C + R_2C)}$$

with natural frequency

$$\omega_n = \sqrt{\frac{K}{R_1C + R_2C}} \quad , \quad K = \frac{K_d K_o}{N}$$

and damping factor

$$\zeta = \frac{\omega_n R_2 C}{2}$$

The digital blocks of the digital PLL (Figure 2.5, the PFD and the divider are digital block) can be integrated in a SoC, It can close to the network interface and control blocks. The analog parts (LPF and VCO) are often located off chip. Then, the

one bit representation of the phase error by the PFD is very advantageous. Since it only one pin is used to transfer the digital phase information to the analog loop filter. In total two pins are required one tri-state output and one input for the VCO output signal.

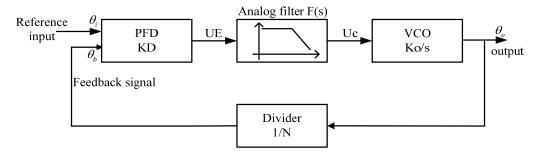


Figure 2.5 Block diagram of a digital PLL with digital block.

#### **All Digital PLL**

In all-digital PLLs (ADPLL) all analog building blocks are replaced by a digital representation. All relevant PLL signals are binary numbers instead of continuous voltages. Thus, the phase frequency detector introduced in section 2.2.2 is modified to output a quantized number representing the phase error.

As shown in Figure 2.6, the ADPLL is composed of a digital phase frequency detector, a digital loop filter, a digitally controlled oscillator, and a divider. The phase frequency detector detects the phase difference of the two clocks and sends the detection result to the digital loop filter. The digital loop filter receives the signal produced by the PFD, and produces a set of digitally controlled signals (binary signals) to control the DCO. The output of the DCO is sent to the divider to divided into the lower frequency range. The divider sends the divided clock to the PFD and completes the loop.

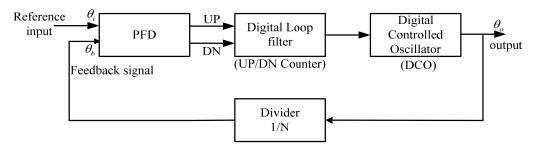


Figure 2.6 Block diagram of an all digital PLL.

In general, there are two types of ADPLL depending on the DCO clock source: (1) to use fixed high speed clock as indicated in [6,11] to form a DCO, (2) to synthesis clock internal based on a DCO circuit as [12,13]. Furthermore, the standard cell based implementation of DCO [14] will also be discussed because of popularity.

#### (1). The DCO with Fixed High Speed Clock:

Figure 2.7 shows the ADPLL with fixed high speed clock and accumulator in [15].

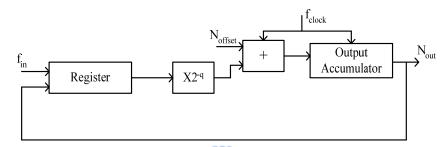


Figure 2.7 ADPLL with fixed high speed clock to form DCO in [15].

The input is a binary fin, and the output is to be a number that has an average repetition rate of fin, but follows the input with a closeness that depends on the loop parameters. The DCO consists of an accumulator and high speed clock  $f_{clock}$ . Its output is a number that changes each clock cycle by an amount equal to its input N2. Each time the output accumulator reaches its capacity  $N_{max}$ , it recycles to 0. Thus, one cycle is represented by  $N_{max}$ , and the output phase of the output accumulator is :

$$\Phi_{out} = (\frac{N_{out}}{N_{max}})$$
 cycles

The output frequency is

$$f_{out} = \frac{\Delta \Phi_{out}}{\Delta t} = (\frac{N_2}{N_{\text{max}}}) \cdot f_{clock}$$

Since the output is incremented by N2 each cycle of the output accumulator. The register stores the value of  $N_{out}$  at each cycle of the input signal fin. The register thus functions as a phase detector and zero order hold. Then, the phase error will be inversed and multiply with  $2^{-q}$ . There are two sampling processes occurring in the simple loop. One is in the register at fin. Another is in the output accumulator at  $f_{clock}$ .

The stability of this simple loop can be represented by using z-transform. The closed loop of Figure 2.7 is

$$H(z) = \frac{K}{z - 1 + K}$$
 where  $K = 2^{-q} (\frac{f_{clock}}{f_{in}})$ 

#### (2). Direct DCO Synthesis Clock:

If the high speed clock is available, such as in SoC, and the target operation's speed is not very high, then DCO with fixed high speed clock can be the choice. However, it may consume large power due to high speed clock operation. The external high speed clock is not always feasible. It requires extra pin and another high-speed quartz oscillator when the target application is for on-chip clock multiplication. In recent years, ADPLL of type is more popular and even applied frequency synthesis for RF wireless application. An ADPLL with high resolution DCO as shown in Figure 2.8 was proposed in [12].

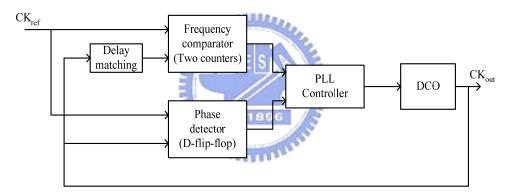


Figure 2.8 ADPLL with direct DCO synthesis clock [12].

This ADPLL achieved fast locking within 50 reference clock cycles as compared with conventional charge pump PLL based clock generator. The fast locking time was achieved with modified binary searching algorithm. It separated the frequency acquisition and phase acquisition. It did not utilize the three state PFD and frequency divider. A high resolution frequency comparator with matching delay line was utilized to achieve frequency accuracy under 0.1% error ratio. A high resolution ring oscillator with 16 bit control word was implemented to generate the accurate frequency output. The DCO will de turns on and disable after 30-40 iterations for frequency comparison. An anchor register is needed to store the baseline frequency. After frequency acquisition is completed. The PLL starts to trace the phase of the reference clock. The phase tracking process was performed with a phase control algorithm and a phase

detector. It contains phase gain controller and two series connected, edge triggered D flip-flops. The phase acquisition process can be finished within 10 reference clock cycles. After the frequency acquisition and phase acquisition. The ADPLL enters phase and frequency tracking process. Many ADPLL variants follow this ADPLL approach, such as [16]. However, the cost of this chip area is extremely high due to DCO. Another small area DCO was proposed in [16]. Those DCO designs were required to be with full custom layout. The specific transistor sizing of DCO comes to be with changes in design specifications.

#### (3). Standard Cell Based DCO:

A standard cell based implementation of all digital clock generator [14]. It based on structure of digital PLL that can be divided into five main parts: the PFD, the loop controller, the loop filter, the DCO, and programmable divider as shown in Figure 2.9. The key issue is that all of the elements are designed form standard cell library without any full-custom layout.

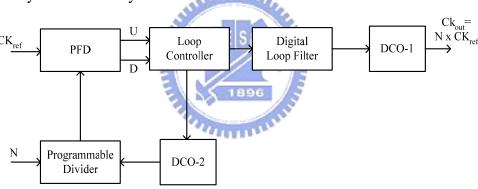


Figure 2.9 Function block of ADPLL in [14].

The function of programmable divider is simply to slow the DCO output frequency for comparison. The loop controller generates the digital commands to track the DCO output clock based on the results from the PFD. Two extra digital pulse amplifier circuits are required to minimize the dead zone of the PFD, as indicated in [14]. However, the control code may have small variations due to the following factors: the PFD's dead zone, the DCO's finite resolution. An average loop filter is necessary to filter out the rippling and produce a smoother digital controlled word with less jumping. Additionally, two DCOs are required for low output jitter to reduce the noise and jitter associated with input reference. This requirement leads to a highly complex and expensive design.

## 2.3 Summary

PLL based clock generator is a trade-off lock-in time, area cost, power consumption, jitter performance, circuit complexity and design time. Thus, it is very challenge to design one PLL clock generator for all applications. The conventional charge-pump PLL based clock generators for microprocessor as indicated [17]. It can accomplish good jitter performance as well as low power consumption. However, the on-chip loop filter occupied a lot of chip area and slow lock-in time. Furthermore, it required long design time due to circuit complexity. Therefore, those clock generators are also only suitable specific application. The application can not be applied a variety of multiplication ranges.

In conventional PLL based clock generator design, fast acquisition requires tuning the free-running frequency near the desired frequency in advance or to increase the loop bandwidth. The exact VCO tuning range is not easy to be achieved, since there always has process variations, voltage variation, and temperature variations (PVT variations).

In the analog PLL, the digital PLL and the all digital PLL, they have many advantages and disadvantages respectively. We compare and illustrate them in Table 2.1

	Analog PLL	DPLL	ADPLL
Design methodology	Analog Mixed-mode		Digital
Design cycle	Slow	Slow	Fast
Output frequency	High	High	Low
Noise immunity	Poor	Poor	Good

Table 2.1 Phase Lock Loop comparison

Lock time	Long	Long	Short	
Area	Large Large		Small	
Power consumption	Large	Large	Small	
Frequency resolution	High	High	Low	

.



# Chapter 3

## **Clock Generation Circuits**

## Classification

## 3.1 Introduction

This chapter explains the most important features of conventional clock generators. As highlighted in the abstract, the focus of this thesis is on the digital clock generation method. Analog clock generators are thus only mentioned, and not explained in detail.

## 3.2 The Analog Clock Generators

## **Voltage-Controlled Oscillators**

Voltage-controlled oscillators are analog circuits that exist in various architectures. The frequency is controlled with a continuous voltage. Pull-range and jitter performance are strongly related and can vary in a broad range.

Voltage-controlled crystal oscillators (VCXO) use a quartz crystal as a resonator. VCXOs provide excellent jitter performance.

## **Voltage-Controlled Ring Oscillators**

Ring oscillators consist of an odd number of inverting stages connected to a loop. By varying the delay of the stages, the frequency of the oscillation can be controlled. In classical ring oscillators, the delay is varied by changing the supply voltage of the stages. As illustrated in Figure 3.1. The absolute frequency stability and jitter performance of ring oscillators are both limited. Jitter of ring oscillators has been

discussed in various publications.

When employed in a PLL, the absolute frequency stability is guaranteed by the control loop mechanism. Ring oscillators provide very high pull ranges of up to a factor of two.

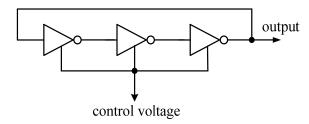


Figure 3.1 A simple ring oscillator.

## 3.3 The Digital Clock Generators

### **All Digital Ring Oscillators**

In contrast to their voltage controlled counterparts, digitally controlled ring oscillators can be built of digital standard cells. Frequency control is obtained by changing the delay in the inverter loop. The operation principle is depicted in Figure 3.2.

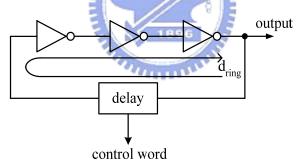


Figure 3.2 All digital ring oscillator.

The output period of the ring oscillator consists of the propagation delays, through the positive and negative edge in the ring. If the delay  $d_{ring}$  is assumed symmetric for both transitions, the frequency of the ring oscillator is

$$f_{ring} = \frac{1}{2d_{ring}}$$

This relationship is illustrated in Figure 3.3. The slop of the curve increases towards small ring delays. Even for very large rings with an oscillation frequency of 25 MHz, the slope at 25 MHz is approximately 1.25 kHz/ps or 50 ppm/ps. Applied to

a ring oscillator, this would require a delay resolution in the ring of 0.02 ps at 25MHz. Digital delay generation with such a high accuracy is not realistic. In Chapter 4, a method for improving the frequency resolution of all digital ring oscillators is proposed.

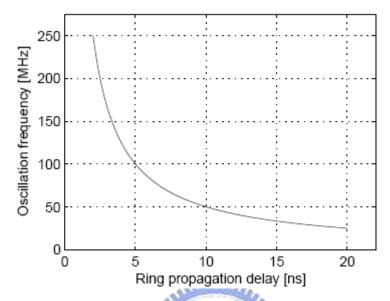


Figure 3.3 Ring oscillator frequency vs. ring delay.

## 3.4 Analysis of the DCO Category

The heart of the ADPLL is a digitally controlled oscillator (DCO). Like most voltage-controlled oscillators, the DCO consists of a frequency-control mechanism within an oscillator block. Generally speaking, an odd number of inverters connected in a loop chain become a ring oscillator. The clock period of the ring oscillator is two times the circular loop delay time. Different propagation delay time of the inverter produces different clock period. Besides, a variable number of inverters implement a variable delay. Therefore, there are two parameters to determine the clock period of the ring oscillator. One is the propagation delay time of an inverter and another is the number of the inverters. In terms of tuning these two parameters, there are many designs of the DCOs that have been presented.

## Standard cell based DCO Design

Figure 3.4 shows a typical ring-oscillator which is very popular architecture in

most ADPLL designs. The main advantage is that the oscillator can be implemented by standard-cell library.

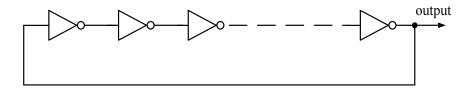


Figure 3.4 A typical ring-oscillator.

The modified architecture is shown in Figure 3.5 [18]. The enable signal powers the ring-oscillator. The path selection consists of tri-state inverters. The path selections from p1 to p4 are used to select different delay time of ring-oscillator to change output frequency. The problem of the architecture is a large parasitic capacitance at node 1 in Figure 3.5, and the DCO resolution is poor due to no fine tune cell being applied.

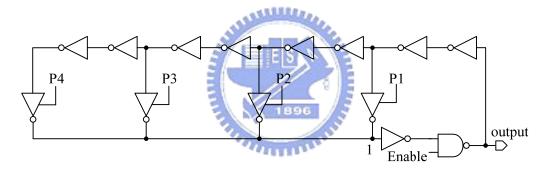


Figure 3.5 Modified architecture in [18].

An improved DCO architecture is showed in Figure 3.6 [14]. It is separated into two stages: a coarse-tuning stage and a fine-tuning stage. To avoid large loading capacitance appearing in the path selection output, the path selector is partitioned into two stages. In the first stage, sixteen coarse-tuning delay blocks select a partial output. The second stage path selector will select the final output.

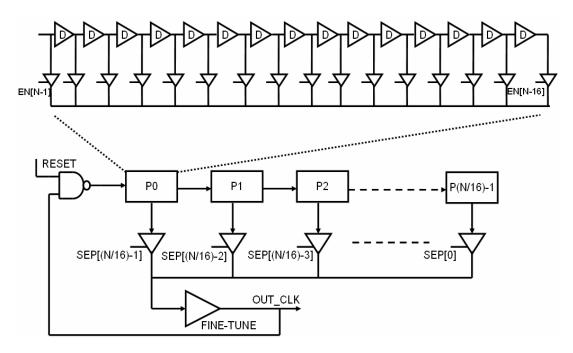


Figure 3.6 An improved DCO architecture in [14].

A cell-based digital controlled oscillator is shown in Figure 3..7[19]. It is a multiple path selection DCO with a delay matrix. When searching frequency, the path selection works as coarse search and the delay matrix works as fine search. The delay matrix consists of several parallel tri-state inverters. Its disadvantage is the large parasitic capacitance in the output node of the path selection.

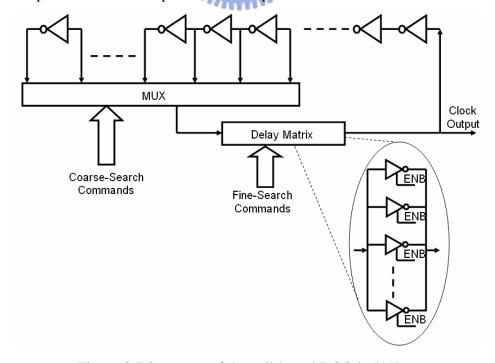


Figure 3.7 Structure of the cell-based DCO in [19].

Another cell-based digital controlled oscillator is shown in Figure 3.8[20]. The oscillator being implemented is a seven-stage ring oscillator with one inverter replaced by a NAND gate for shutting down the ring oscillator during idle mode. To change the frequency of the ring oscillator, a set of 21 tri-state inverters are connected parallel to each inverter. When the tri-state inverters are enabled, additional current is added to drive each inverter stage. Although the DCO has the advantages of being made from all-standard cells, it has disadvantages such as relatively high power consumption and low maximum frequency from high capacitive load in the ring oscillator.

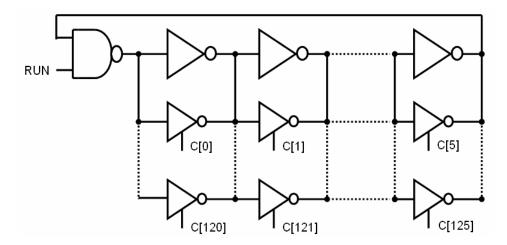


Figure 3.8 DCO using parallel tri-state inverters to adjust frequency in [20].

#### Delay cell DCO design

A DCO structure is showed in Figure 3.9(a) [12]. The ADPLL controls the DCO frequency through the DCO control word. Arithmetically incrementing or decrementing the DCO control word modulates the DCO frequency and phase. The magnitude of the incremental changes to the DCO control word defines the gain, which, in turn, dictates the relative change in DCO frequency ( $\triangle F/\triangle$ DCO control word). As Figure 3.9(a) shows, the requisite odd number of inverting stages in the DCO is obtained by using one enabling NAND gate and eight controllable cells. Figure 3.9(b) illustrates the basic premise of a constituent DCO cell. The sizing ratio of the control devices is 2X to achieve binary weighted control. Hence, the DCO cell can control the propagation delay time with n-bit control word. The disadvantage is the large area overhead.

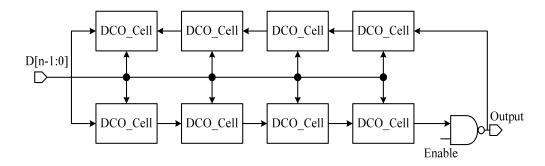


Figure 3.9(a) 8-cell DCO with control bit [12].

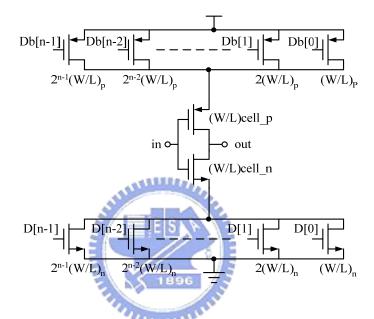


Figure 3.9(b) Constituent DCO cell [12].

Another DCO structure is showed in Figure 3.10[16]. The DCO consists of four paths and four DCO cells. The DCO cell is shown in Figure 3.9(b). The path selection works as the coarse search. The DCO cells work as the fine tune. The area of the DCO in Figure 3.10 is smaller than the area of the DCO in Figure 3.9(a).

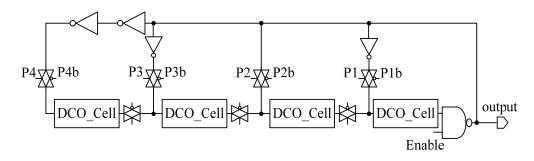


Figure 3.10 Structure of DCO in [16].

An improved DCO architecture is showed in Figure 3.11(a) [21]. The DCO consists of coarse cell, fine cell, unit gain circuit and voltage divider. The DCO control word is the 8 binary weighted control signals. The weighted control signals DCO[4]~DCO[7] control the coarse cell and the others control the fine cell. The switch of the coarse cell is turned on by the Voltage\_A and the switch of the fine cell is turned on by the Vdd voltage or Gnd voltage. By the two stage method, it can save the area and power consumption. The coarse cell of the DCO was shown in the Figure 3.11(b). The fine cell is the same with coarse cell but the Voltage\_A becomes Vdd voltage or Gnd voltage.

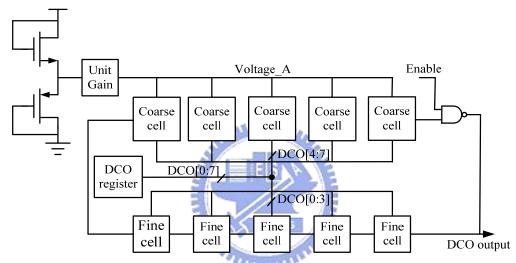


Figure 3.11(a) An improved DCO architecture in [21].

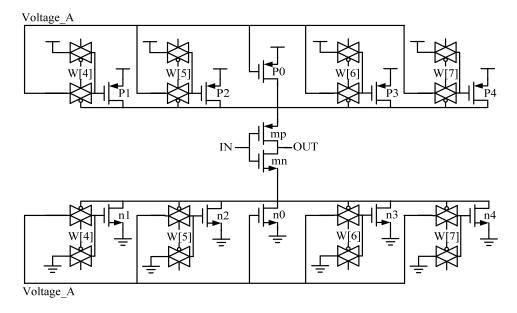


Figure 3.11(a) The coarse cell of the DCO in [21].

# 3.5 Summary

Existent clock generation methods have been explained and the performance has been compared to the requirements mentioned above. Table 3.1 lists the characteristics of conventional clock generation circuits. In the next chapter, a new clock generation methods are proposed.

Table 3.1 Characteristics of various clock generation circuits.

Clock Generation method	Frequency range	Frequency resolution	Intrinsic Jitter	All digital Circuit
VCO	high	high	low , depends on pull-range	No , analog technique
VCXO	very high	high	very low	No , analog technique
Voltage controlled Ring Oscillator	high	high 1896	low	No ,analog Ring delay control
All digital Ring Oscillator	very high	low	low	yes

# **Chapter 4**

# **Digitally Controlled Oscillator with**

# **High Resolution and 8-Phase Output**



Traditional analog circuit design, such as voltage controlled oscillator (VCO), shifts the design paradigm towards more digitally intensive techniques. The digitally controlled oscillator is the key component of all digital PLL. The quality of the output clock is decided by its performance. There are three issues to design a DCO. First, the output clock of a DCO is discrete, so the resolution of a DCO should be sufficiently high to maintain acceptable jitter. Second, for searching target frequency and phase easily and efficiently. A DCO has better monotonic response to the DCO control word. Third, a DCO has better noise immunity, so the output clock will not induce large jitter. The noises come from power supply, control word transition, or other condition. Thus, this chapter attempts to propose a high resolution DCO by using transmission gates as novel delay cells.

# **4.2** Basic Concepts of Digitally Controlled Oscillators

#### **Introduction to the fundamental function of DCO**

The fundamental function of a DCO is to provide an output waveform, typically in the form of square wave. The square wave has a frequency  $f_{DCO}$  that is a function of a digital input word D, as follows:

$$f_{DCO} = f(D) = \Delta f \times (d_{n-1}2^{n-1} + d_{n-2}2^{n-2} + \dots + d_12^1 + d_02^0)$$

Typically, the DCO transfer function  $\Delta f \times (d_{n-1}2^{n-1} + d_{n-2}2^{n-2} + \dots + d_12^1 + d_02^0)$  is defined so that either the frequency  $f_{DCO}$  or the period of oscillation  $T_{DCO}$  is linear

with D, generally with an offset. For example, a DCO transfer function that is linear in frequency is typically expressed as:

$$f(D) = f_{offset} + D \cdot \Delta f$$

Where:  $f_{offset}$  is a constant offset frequency and  $\Delta f$  is the frequency quantization step.

Similarly, a DCO transfer function that is linear in period is typically expressed as:

$$T(D) = T_{offset} + D \cdot \Delta T$$

Where:  $T_{offset}$  is a constant offset period and  $\Delta T$  is the period quantization step. It is evident that, since the DCO period T(D) is a function of quantized digital input D. The DCO can not generate a continuous range of frequencies. In this regard, the quantization granularity of the DCO period sets some fundamental limits on the achievable jitter of an all digital PLL. It is of course desirable to have a fairly small quantization step size.

#### **Analysis of the DCO Design Approaches**

#### (1). The DCO constructed with the DAC and the VCO:

The DCO in [22] is directly utilized digital-to-analog converter (DAC) and conventional voltage controlled oscillator (VCO) as shown in Figure 4.1. Another DCO in Figure 4.2[23] is converted the frequency directly to the digital value, and change the gain for VCO control adaptively. However, to design a high resolution DAC is extremely difficult. In addition, the VCO is an analog block that is easy to be influenced by power and substrate noise. The chip area cost is very high due to DAC

and VCO.

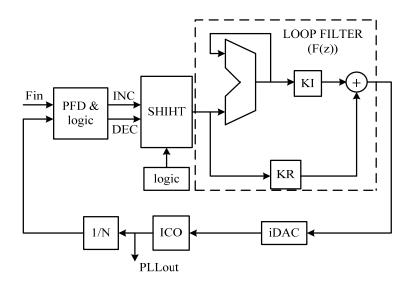


Figure 4.1 The DCO constructed with the DAC and the VCO in [22].

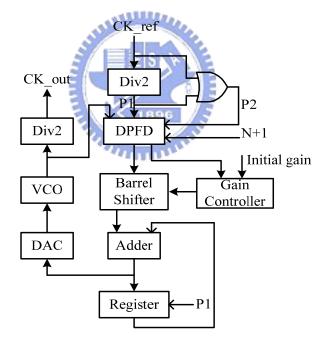


Figure 4.2 The DCO constructed with the DAC and the VCO in [23].

#### (2). The DCO constructed with high speed clock and divider:

The common type of conventional DCO includes a high frequency oscillator in combination with a programmable frequency divider. Figure 4.3 shows the DCO. A programmable frequency divider receives an n-bit digital control word D which indicates the divisor values. The output DCO (CLK) signal is to be divided from a high speed oscillator (HFCLK).

The period quantization step  $\Delta T$  is limited by the high frequency oscillator (HFCLK) in this arrangement. Low jitter operation thus requires oscillator to operate at an extremely high frequency. For example, a 100 ps step between periods require high frequency oscillator and programmable counter to operate at 10GHz. This will consume a lot of power consumption.

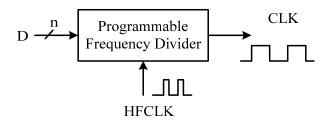


Figure 4.3 The DCO constructed with high speed clock and divider.

#### (3). The DCO constructed with variable length ring oscillator:

Because of the speed limitation, other conventional DCO approaches directly synthesis a signal, rather than dividing down from a high frequency source. Figure 4.4 shows a variable length ring oscillator. For example,  $2^n$  delay buffer are connected in series. A decoder decodes n-bit digital control word D into  $2^n$  control lines. If the propagation delay time of each buffer stage is Tbuffer. Then the period quantization step is thus  $2^*$ Tbuffer, which is typically an improvement over Figure 4.3's design. However, the period quantization step still may be too coarse for many applications.

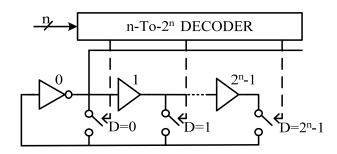


Figure 4.4 The DCO constructed with variable length ring oscillator.

#### **Enhance Fine Resolution of the DCO design**

The basic skill to enhance the fine resolution of DCO is to enhance overall driving capability. The methods are to adjust the overall resistance ( $\mathbf{R}$ ), or to adjust capacitance ( $\mathbf{C}$ ), or to adjust inductance ( $\mathbf{L}$ ) as shown in Figure 4.5.

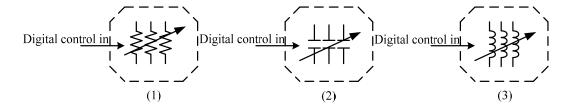


Figure 4.5 General mechanism for enhance of fine tune in the DCO.

#### (1). The mechanism are to adjust the resistance:

As shown in Figure 4.6[24], the pull-down stack uses a transistor array in which multiple rows are allowed. The transistor array actually forms the digitally adjustable resistor. Each bit of the control signal b[n-1:0] is connected to the gate of one transistor in the array.

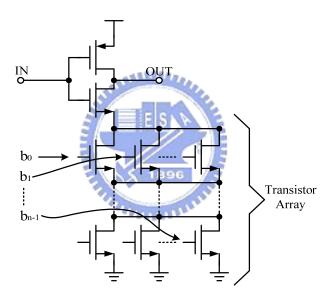


Figure 4.6 The mechanism are to adjust the resistance.

#### (2). The mechanism are to adjust the capacitance:

As shown in Figure 4.7[25], has developed a novel DCV using three-input NAND gates for DCO design. The DCV uses the gate capacitance difference of NAND gates under different digital control inputs to build digitally controlled varactors (DCV) as shown in Figure 4.7(a). Figure 4.7(b) shows the equivalent circuit of Figure 4.7(a), an initial capacitance (C1) parallels with a capacitance difference with ( $\Delta C$ ). The D input controls the capacitance ( $\Delta C$ ) in the output (Out) node. The marked transistor (Mn2) produces a large capacitance difference under different D

states.

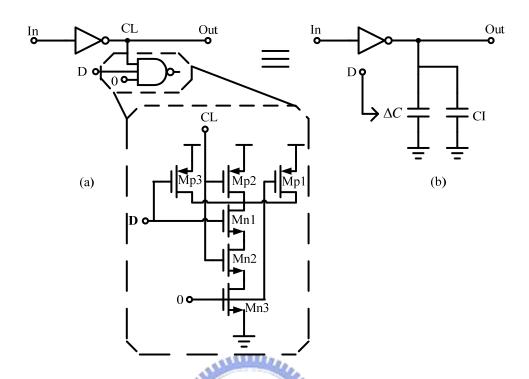


Figure 4.7 The mechanism are to adjust the capacitance.

## Fine Tune in Standard Cell Design

For most digital applications, a standard cell description of the digitally controlled oscillation simplifies the design, and it can be easily ported to different processes in a very short time period.

The fine delay steps determine the resolution of the delay line. Three fine delay generation methods are illustrated in Figure 4.8, Figure 4.9, and Figure 4.10. The first one consists of a multiplexer and two identical buffers. As shown in Figure 4.8 [26]. One of the buffers is loaded by a small capacitance, while the other is not. This results in a delay difference between the two paths Tfine that depends on the load and on the drive strength of the buffers, but not on the absolute delays of the buffers. The minimum delay Tmin of this fine-delay line is the sum of Lfine. The Lfine is propagation delays of all unloaded buffers with their corresponding multiplexers. In order to reduce the minimum delay, the buffer can also be replaced by inverters and non-inverting multiplexers by inverting multiplexers. Both inverting cells are significantly faster in most standard-cell libraries than their non-inverting counterparts.

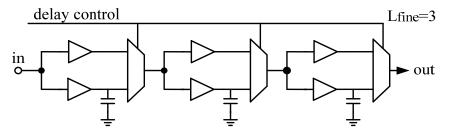


Figure 4.8 a multiplexer and two identical buffers structure.

The second type shown in Figure 4.9 [27], depending on the technology above, replacing the multiplexers and the buffers by NAND gates can improve the minimum delay further. The main idea is using the delay different of paths. For example, the capacitances and output strengths of different pins are close for a NAND gate in standard-cell library. The timing delay difference from different input pins to the same output pin approximates to the intrinsic difference.

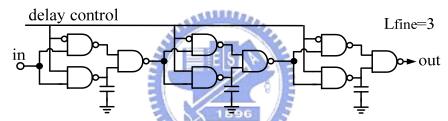


Figure 4.9 replace the multiplexers and the buffers by NAND gates.

The third type consists of a bank of tri-state buffers driving the same node. As shown in Figure 4.10[19]. The number of enabled buffers influences the delay of the cell. The frequency resolution is decided by the minimum scale of a delay matrix. It is important for systems not only to maintain a table clock but also to ensure minimum frequency error. In order to improve the linearity of the delay sequence, some buffers may drive permanently, and the increment of activated buffers may be not constant.

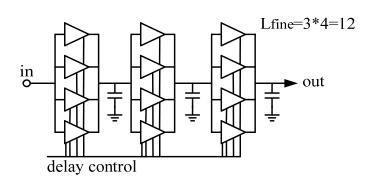


Figure 4.10 a bank of tri-state buffers.

Fine delay generation methods, the Figure 4.8 and Figure 4.9 solutions are based on two identical buffers with different loads. The Figure 4.10 uses the drive strength of a bank of tri-state buffers to control the delay.

Another example of DCO implement by an and-or-inverter(AOI) cell and or-and-inverter(OAI) cell with two parallel tri-state inverters was proposed in Figure 4.11[14]. The basic method is to adjust the driving capability with resistance control. Its resolution step is non-uniform and sensitive to power-supply variation because it is based on AOI-OAI cell to change the delay resolution. In addition, this technique also requires an additional decoder for mapping AOI-OAI cell control inputs.

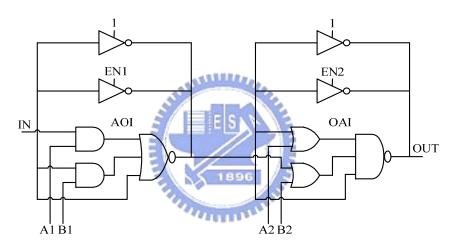


Figure 4.11 High resolution delay cell.

# **4.3** The Proposed Fine Tune Delay Cell with High Resolution

## The DCO with High Resolution Delay Cell

The proposed DCO, like most voltage controlled oscillators or delay control, employs a frequency control mechanism located inside an oscillator block. Two parameters are used to modulate the output frequency of a ring oscillator. Namely two parameters are the propagation delay time of each delay cell, and the total number of delay cells in the close loop. Thus, we developed a novel delay cell using transmission

gate in the fine tune cell design of DCO. The proposed DCO improves delay resolution and demonstrates monotonic delay behavior with respect to digital control codes.

Basically, two main techniques exist for design a fine resolution in DCO with shunt capacitor. One technique changes the MOS driving strength dynamically using a fixed capacitance loading and achieves a fine resolution [28]. Meanwhile, the other uses the shunt capacitor technique to fine tune capacitance loading and achieves high resolution [29]. Figure 4.12 shows the conventional control mechanism with the shunt capacitor circuit. In Figure 4.12, Mc serves as a capacitor. The gate of transistor Mctrl (Dctrl) controls the discharge current and charge current. Hence, Dctrl can control the delay resolution from In to Out.

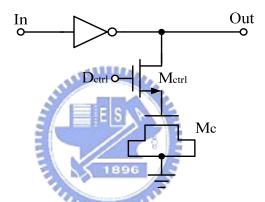


Figure 4.12 Conventional control mechanism with shunt capacitor.

Thus in previous design, as shown in Figure 4.10, the delay matrix uses parallel tri-state buffers to enhance the resolution of the delay cell. However, the area cost and the power consumption for the delay matrix is too large to be used in a low cost and low power design. As shown in Figure 4.11, its area cost and power consumption is low, the average resolution of the delay cell is about is 5ps.

### The Proposed High Resolution Delay Cell

As mentioned before, there are two main techniques existing for design a fine resolution in DCO. However, the proposed a method of changing capacitor value to modulate frequency with fixed current value.

Figure 4.13(a) illustrates a novel delay cell using a transmission gate. The proposed method controls the capacitance between gate and source or between gate

and drain. In Figure 4.13(a), the gate capacitance of transmission gate at node  $C_L$  depends on control node  $V_{fc}$  's value. The total gate capacitance at node  $C_L$  varies with  $V_{fc}$  input states. Figure 4.13(b) shows the equivalent circuit of Figure 4.13(a), an initial capacitance ( $C_I$ ) parallels with a capacitance difference ( $\Delta C$ ). The  $V_{fc}$  input controls the capacitance ( $\Delta C$ ) in the output (Out) node.

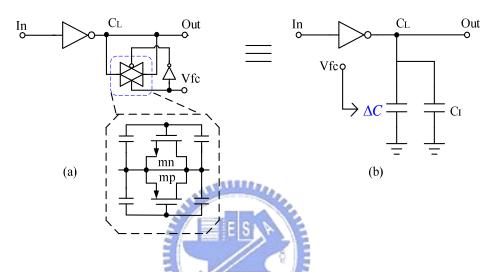


Figure 4.13 Proposed delay cell with transmission gate. (a) Circuit with digital control. (b) Equivalent circuit with  $\Delta C$  capacitance.

Figure 4.14 shows the gate capacitance difference characteristic which is simulated using the Hspice circuit simulator. Figure 4.14(a) shows the gate capacitance of transmission gate when the mp and the mn is "on" or "off". Figure 4.14(b) illustrates the gate capacitance of the mp and the mn when them is "on" or "off". As Figure 4.14(b) shown, the capacitance value of  $\Delta C$  is estimated at "fF" grade. As described in [30], the transmission gate equivalent resistance is estimated at "k-ohm" grade. Therefore, the  $\Delta T$  can be achieved "ps" grade.

$$\Delta T = \mathbb{R}^* \Delta C \rightarrow (ps = k\Omega * fF)$$

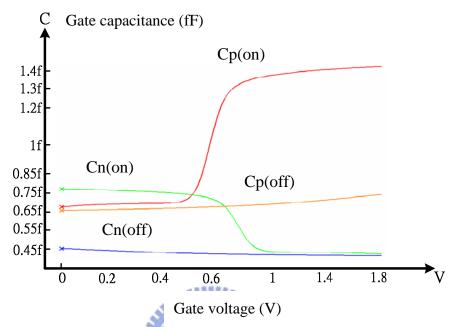


Figure 4.14(a) The gate capacitance of transmission gate.

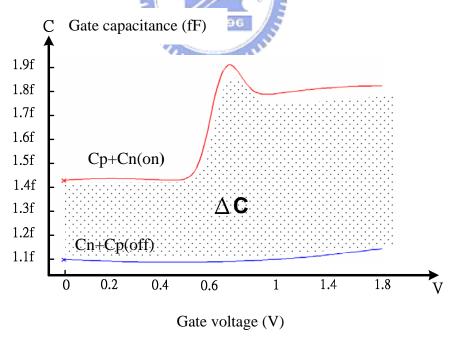


Figure 4.14(b) The gate capacitance of transmission gate.

Figure 4.15 illustrate the difference of equivalent capacitor value from drain with MOS "on" or "off" to modulate high timing resolution. When MOS is "on", the

equivalent capacitor value from drain will be larger. When MOS is "off ", the equivalent capacitor value from drain will be smaller. Assume the fine-tune section has a 6-bit control word and adopt a binary weighted control mechanism.

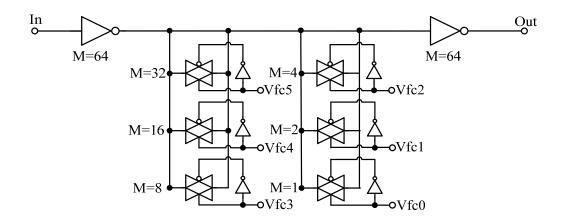


Figure 4.15 High resolution delay cell.

Figure 4.16 illustrate the high resolution delay cell simulation result. Fine-tune input control word rang from "000000" to "111111". Thus, a total of 64 different delays can be provided. In this simulation, the average resolution is about 125.7fs = [8.05ps/64]. In the meantime, delay time versus control word is very linear. For gigabit optical communication, this resolution is quiet sufficient.

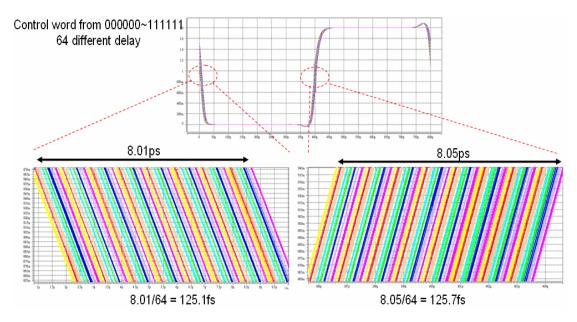


Figure 4.16 High resolution delay cell simulation result.

## **4.4** Structure of the Proposed DCO

### Structure of the DCO and Design Guide

This DCO design applications demand high resolution, high speed, and multi-phase output. Namely, the design target is 1.25GHz, 8-phase output, and high resolution. As shown in Figure 4.17, the DCO is consisted of four delay elements (DCO-cell) with differential operation frequency and 8-phase output. The oscillation frequency depends on the equivalent load resistance and equivalent capacitance of the delay element. By tuning the equivalent capacitance can obtain the desire oscillation frequency. In the test chip, the DCO is implemented with TSMC 0.18um 1P6M CMOS process.

Figure 4.18 illustrates the structure of the proposed cell-based DCO-cell with 10-bits binary weighted control. The proposed DCO-cell structure is separated into three stages, the coarse-tuning stage, the medium-tuning stage and the fine-tuning stage. Besides, the DCO-cell still contains the trigger circuit, as shown in Figure 4.19. The higher three bits of the control code are for coarse-tuning stage. The lower four bits of the control code are for fine-tuning stage. Other three bits of control code are for medium-tuning stage. The coarse tuning stage is consisted of an always on of tri-state inverter and three tri-state inverters. It is a matrix structure, whose characteristics are determined by both the combination and number of tri-state inverters. Note that the dynamic control range is determined by the combination of tri-state inverter matrix.

The medium-tuning stage is consisted of three proposed hysteresis delay cell (HDC). The HDC contains two tri-state inverters. The operation concept of HDC is to control driving current to obtain different propagation delay. When tri-state inverter of HDC is enabled, the output signal of enable tri-state inverter has the hysteresis phenomenon in the transition state to produce different delay times from the delay chain. As shown in Figure 4.18, addition to the latch between two signal paths. The latch is consisted of two minimum size inverters. The way of adding small latch forces two signal paths differential is called "pseudo-differential". Both side of latch will force two signal paths to be 180 degree out of phase.

In order to increase frequency resolution of the DCO, the fine-tuning delay cells are added. The fine-tuning stage is consisted of four transmission gates. The circuit of

fine-tuning delay cell is shown in Figure 4.13(a). The detail information about how to design the fine-tuning delay cell is discussed in Section 4.3.

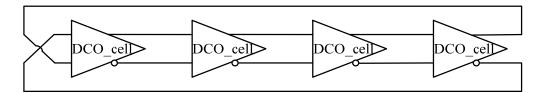


Figure 4.17 The proposed DCO architecture.

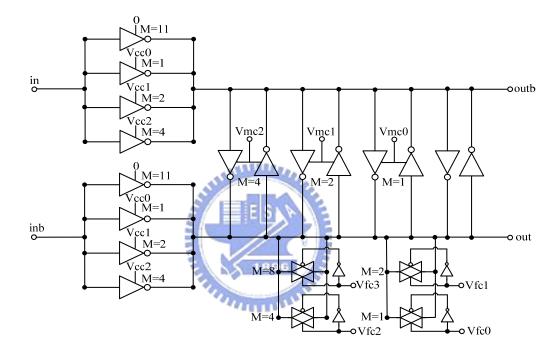


Figure 4.18 The proposed DCO-cell architecture.

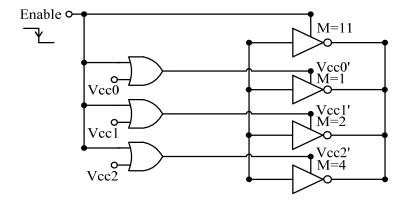


Figure 4.19 The trigger circuit of the DCO.

## **Design of the DCO**

The minimum required voltage gain and contributed phase shift per stage are derived based on "Barkhausen criteria". Thus, we analyze the DCO from the small-signal model. Figure 4.20 illustrates the small-signal model of the DCO-cell structure. Figure 4.21 represents the parameters including the transconductance, the output impedance, and the output capacitance of the coarse stage, the medium stage, and the fine stage.

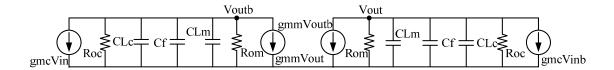


Figure 4.20 The small-signal model of the DCO-cell.

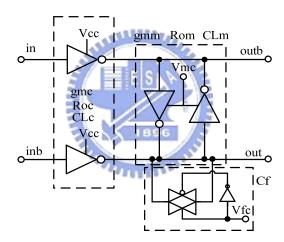


Figure 4.21 The parameter of the DCO-cell

The small-signal model equation derived from Figure 4.20 is shown as follows

$$\begin{split} [g_{mm} \cdot v_{outb} + g_{mc} \cdot v_{inb}] + \frac{v_{out}}{R_{oc}} + \frac{v_{out}}{R_{om}} &= -[SC_{Lc} + SC_{Lm} + SC_f] \cdot v_{out} \\ [g_{mm} \cdot v_{out} + g_{mc} \cdot v_{in}] + \frac{v_{outb}}{R_{oc}} + \frac{v_{outb}}{R_{om}} &= -[SC_{Lc} + SC_{Lm} + SC_f] \cdot v_{outb} \end{split}$$

The transfer function of the DCO-cell(H(s)) is shown as follows

$$H(s) = \frac{V_O(s)}{V_i(s)} = \frac{g_{mc}}{-g_{mm} + \frac{1}{R_{OC}} + \frac{1}{R_{Om}} + S(C_{Lc} + C_{Lm} + C_f)}$$
(1)

where  $g_{mc}$  is the transconductance of the coarse stage;  $g_{mm}$  is the transconductance

of the medium stage;  $R_{oc}$  is output impedance of the coarse stage;  $R_{om}$  is output impedance of the medium stage;  $C_{Lc}$  is load capacitance of the coarse stage;  $C_{Lm}$  is load capacitance of the medium stage;  $C_f$  is equivalent capacitance of the fine stage.

The transfer function of each stage denotes  $\frac{A_0}{(1+\frac{S}{\omega_0})}$ . Hence the loop gain of the

four stages is

$$H(s) = \frac{A_0^4}{(1 + \frac{S}{\omega_0})^4} \tag{2}$$

Equation (3) can be derived from equations (1) and (2):

$$H(s) = \frac{\left[\frac{g_{mc}}{(-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})^4}\right]^4}{\left[1 + \frac{S(C_{Lc} + C_{Lm} + C_f)}{(-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})^4}\right]^4}$$
(3)

The 3-dB bandwidth of each stage can be derived from equation (3):

$$\omega_0 = \frac{(-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})}{(C_{LC} + C_{Lm} + C_f)}$$
(4)

For the circuit to oscillate, each stage must contribute a frequency-dependent phase shift of  $^{180}/_{4} = 45^{\circ}$ . The oscillating frequency is given by  $\tan^{-1} \frac{\omega_{osc}}{\omega_{0}} = 45^{\circ}$ . Hence

 $\omega_{osc}$  is equal to  $\omega_0$  . The minimum voltage gain of each stage can be derived as follows

$$\frac{\frac{g_{mc}}{(-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})}}{\sqrt{1 + (\frac{\omega_{osc}}{\omega_0})^2}} = 1$$
(5)

The minimum voltage gain of each stage can be derived from equations (2) and (5) as  $A_0 = \sqrt{2}$ .

The  $\omega_{osc}$  of the ring oscillator is derived based on "Barkhausen criteria

 $(|H(j\omega_{osc})|=1)$ ". This is

$$\omega_{osc} = \sqrt{\frac{g_{mc}^2 - (-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})^2}{(C_{Lc} + C_{Lm} + C_f)^2}}$$
(6)

From equation (6), the oscillation frequency of the ring oscillator can be derived:

$$f_{osc} = \frac{1}{2\pi} \sqrt{\frac{g_{mc}^2 - (-g_{mm} + \frac{1}{R_{oc}} + \frac{1}{R_{om}})^2}{(C_{Lc} + C_{Lm} + C_f)^2}}$$
(7)

From equation (7), the maximum oscillating frequency ( $f_{max}$ ) and the minimum oscillating frequency ( $f_{min}$ ) can be derived as follows:

$$f_{\text{max}}: g_{mm(\text{min})} \cong \frac{1}{R_{OC}} + \frac{1}{R_{Om}} \rightarrow f_{\text{max}} \approx \frac{1}{2\pi} \cdot \frac{g_{mc(\text{max})}}{(C_{IC} + C_{Im} + C_f)}$$
 (8)

$$f_{\min}: g_{mm(\max)} >> \frac{1}{R_{oc}} + \frac{1}{R_{om}} \Rightarrow f_{\min} \approx \frac{1}{2\pi} \cdot \sqrt{\frac{g_{mc(\min)}^2 - g_{mm(\max)}^2}{(C_{Lc} + C_{Lm} + C_f)^2}}$$
 (9)

From equations (8) and (9), the operating frequency range ( $f_{range}$ ) can be derived as follows:

$$f_{range} \approx f_{\text{max}} \cdot \left[1 - \sqrt{\left(\frac{g_{mc}(\text{min})}{g_{mc}(\text{max})}\right)^2 - \left(\frac{g_{mm}(\text{max})}{g_{mc}(\text{max})}\right)^2}\right]$$
(10)

From (10), 50% frequency-tuning range can be achieved with a transconductance ratio of the coarse stage and the medium stage ( $\frac{g_{mm}}{g_{mm}}$ ) being  $\sqrt{6/13}$ .

## **Analysis of the DCO**

There are two issues in designing the desired DCO; a sufficiently high resolution to maintain acceptable jitter, a monotonic response of the control word to the oscillation frequency, and high noise immunity.

The clock period control range of the DCO consists of several sections. The control range of each control word determines the clock period of each section. The control range must be larger than the clock period difference between each two neighbor control words. Otherwise, there are frequency gaps in each two neighbor

control words. Moreover, in order to increase the tolerance of the process variation, the overlap of the clock period must be large enough.

This basic concept of the clock control period range is illustrated in Figure 4.22. Having these basic concept and design issues, we can design the DCO in detail based on above discussions.

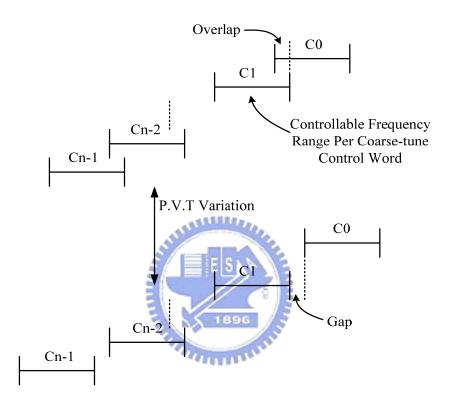


Figure 4.22 Influence of PVT variations on the controllable frequency range.

## 4.5 Simulation Results and Layout

Follow the methods in Section 4.3 and Section 4.4, we propose the DCO architecture as Figure 4.17, Figure 4.18, and Figure 4.19. Figure 4.23 illustrates the clock period of the proposed DCO at three different corner cases. As shown in Figure 4.23, three corner cases all cover 800ps for the center frequency of 1.25GHz.

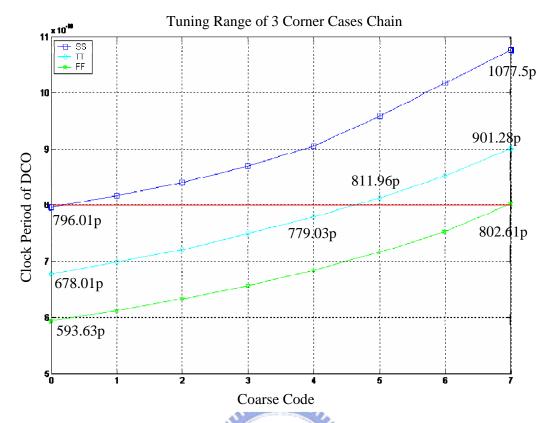


Figure 4.23 The clock period range of the DCO at three different corner cases.

Figure 4.24 shows monotonous curves of tuning code according to medium tuning frequency of the DCO at TT corner.

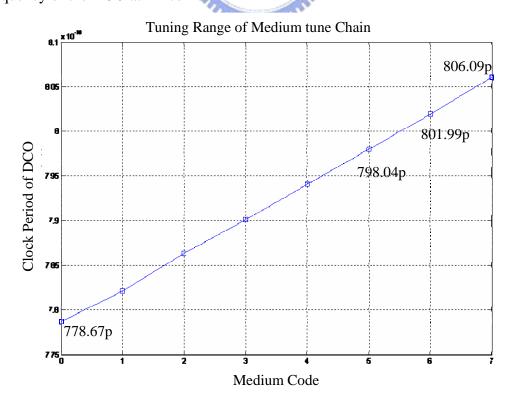


Figure 4.24 Tuning range of medium stage.

Figure 4.25 shows monotonous curves of tuning code according to fine tuning frequency of the DCO at TT corner. And delay range of the fine tune chain is about 6.07ps. Therefore, the average resolution is about 0.38ps.

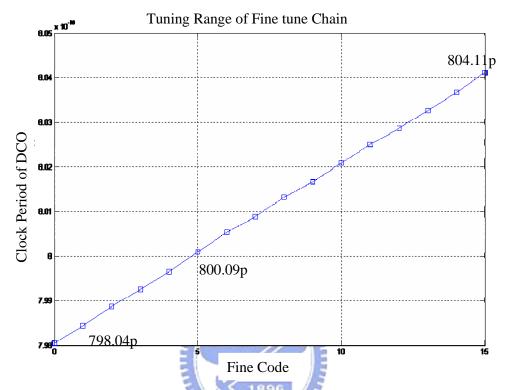


Figure 4.25 Tuning range of fine stage.

## Gap issue

In order to consider period gaps in each two neighbor control words, the gaps issue is analyzed. As shown in Figure 4.26(a) and Figure 4.26(b), period in each two neighbor control words are overlapped at TT corner. Thus, the proposed DCO has no period gaps in each two neighbor control words.

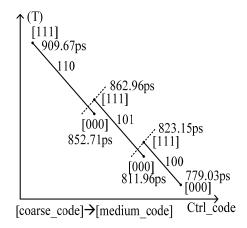


Figure 4.26(a) The coarse-code vs. medium-code period overlap diagram.

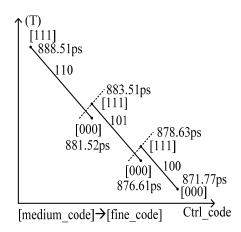


Figure 4.26(b) The medium-code vs. fine-code period overlap diagram.

Table 4-1 shows the form of period overlap at three different corner cases. As shown in Table 4-1, the periods in two neighbor control words are overlapped at three different corner cases. Thus, the proposed DCO has no period gaps in each two neighbor control words at three different corner cases.

Table 4-1 The form of period overlap.

		Coarse_tune	Medium_tune	Fine_tune
TT	Tuning range		56.96ps	6.99ps
	resolution	48.6ps	4.95ps	
SS	Tuning range		67.23ps	7.5ps
	resolution	59.5ps	5.5ps	
FF	Tuning range		46.8ps	6.45ps
	resolution	41.1ps	4.33ps	

#### Layout

The digitally controlled oscillator is implemented in TSMC  $0.18 \,\mu$  m 1P6M CMOS process. The layout of this chip is shown in Figure 4.27. The core area is

"  $310um \times 220um$ ", while the chip area is  $680um \times 680um$ ". The post-layout simulation result summary is shown in Table 4-2.

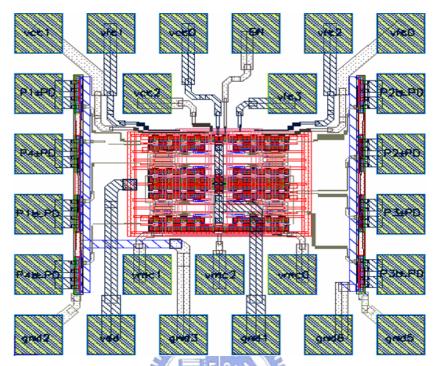


Figure 4.27 The layout of the proposed digitally controlled oscillator.

Table 4-2 The summary of the performance

Function	Digitally Controlled Oscillator	
Process	0.18um@1.8V	
Control word length	Coarse_tune :3 bit , Medium_tune :3 bit Fine_tune :4 bit	
Control word type	Coarse_tune :Binary,Medium_tune :Binary Fine_tune :Binary	
LSB resolution	Avg. Gain: 0.38 ps/code	
Output frequency	1.06GHz ~ 1.50GHz	
Core Area	310um x 220um	
Chip Area	680um x 680um	
Multi-phase Output	8 - phase Output	
Power consumption	34.1mW @ 1.25GHz	

## 4.6 Comparisons and Summary

#### **Comparisons**

Table 4-3 shows the comparisons among different DCOs. As shown in Table 4-3, the proposed DCO with multi-phase output achieves the finest LSB resolution.

This work TCAS2 07[33] JSSC 05[32] ASSCC 05[31] TCAS2 05[25] JSSC 03[14] Function Process 90nm@1.0V 0.18um@1.8V 0.18um@1.8V 0.18um@1.8V 0.35um@3.3V 0.35um@3.3V **DCO** 1.06 ~ 1.5 GHz 191 ~ 952 MHz | 413 ~ 485 MHz |  $0.75\sim1.8\;GHz$  $18\sim 214\;MHz$  $45\sim450\;MHz$ output range LSB 0.38 ps1.47 ps 2 ps 0.6 ps 1.55 ps 5 ps resolution Power 34.1mW 140uW 170~340uW 26.8 mW18mW 50mW consumption @1.25GHz @ 670MHz @200MHz (Static only) @200MHz @500MHz 100um x 50um Area 310um x 220um 100um x 400um 200um x 200um Multi-phase Yes (8-phase) No No No

Table 4-3 Comparison with existing DCOs.

## **Summary**

Table 4-3 shows the comparisons among different DCOs. As shown in Table 4-3, the proposed DCO with multi-phase output achieves the finest LSB resolution.

In this chapter, the basic DCO concept, the basic DCO design, and fine tune methods are discussed at first. Then, a digitally controlled oscillator with 8-phase output using the transmission gate as digitally controlled fine-tune cell is presented. The proposed DCO is implemented in TSMC  $0.18\,\mu$  m 1P6M CMOS process. It can be operate from 1.06GHz to 1.5GHZ. The average delay resolution of the DCO is 0.38ps. The proposed DCO has multi-phase output, high resolution, and small silicon area suitable for high-speed serial link application.

# **Chapter 5**

## **Conclusions**

## **5.1** Conclusions

This thesis proposed a digitally controlled oscillator has high timing resolution, and multi-phase output (8-phase) for ADPLL. The proposed digitally controlled oscillator can be applied to "a 1.25GHz ADPLL with 8-phase output" and "a 2.5Gb/s data-transceiver architecture". Thus, there are two issues in designing the desired DCO; a sufficiently high resolution to maintain acceptable jitter, a monotonic response of the control word to the oscillation frequency. As the simulation results in Section 4.5, the proposed DCO can achieve the target on above discussions.

The digitally controlled oscillator circuit is consisted of four delay elements (DCO-cell) with differential operation frequency and 8-phase output. This thesis proposes a novel fine-tuning method to change the DCO oscillating frequency slightly. The DCO timing resolution can be improved to about 0.38ps by adding fine-tuning delay stage. The frequency range is about 1.06GHz to 1.5GHz by HSPICE circuit simulation. The proposed digitally controlled oscillator circuit is designed using TSMC 0.18  $\mu$  m 1P6M CMOS process with active die area of  $310 \mu m \times 220 \mu m$ . The

total power consumption of the proposed DCO is 34.1mW when oscillate frequency is 1.25GHz. In this thesis, a systematic design method for the DCO design is also presented. The design methodology proposed can reduce design time and design complexity of the DCO. The conclusion, the proposed digitally controlled oscillator has multi-phase output, high timing resolution, and small silicon area, making it very suitable for SOC applications.



# **Bibliography**

- [1] A. Chattopyadhyay, and Z. Zilic, "GALDS:A Complete Framework for Designing Multiclock ASICs and SoCs", IEEE Trans. On VLSI Systems, Vol. 13, No. 6, pp. 641-654, June, 2005.
- [2] Joseph M. Ingino, Vincent R. von Kaenel, "A 4-GHz Clock System for a High-Performance System-on-a-Chip Design", IEEE Journal of Solid-State Circuits, Vol. 36, No. 11, pp. 1693-1698, Nov. 2001.
- [3] Dennis Buss, B.L. Evans, J. Bellay, W. Krenik, B. Haroum, D. Leipold, K. Maggio, J. Y. Tang, and Ted Moise, "SOC CMOS Technology for Personal Internet Products", IEEE Journal of Solid-state Circuits, Vol. 50, No.3,pp. 546-556, March 2003.
- [4] Anne-Johan Annena, Bram Nauta, R. van Langevelde, and H. Tuinhout, "Analog Circuits in Ultra-Deep-Submicron CMOS", IEEE Journal of Solid-State Circuits, Vol. 40, No. 1,pp. 132-143, Jan. 2005.
- [5] D. H. Wolaver, "Phase-Locked Loop Circuit Design", Englewood Cliffs, NJ: Prentice-Hall 1991.
- [6] R. E. Best, "Phase-Lock loops, Theory, Design and Applications", New-York: McGraw-Hill, 1998, 3<sup>rd</sup> Edition.
- [7] C.-C Chung and C.-Y. Lee, "An New DLL-Based Approach for All-Digital Multiphase Clock Generation", IEEE Journal of Solid State Circuit, Vol. 39, No. 3, pp. 469-475, March 2004.
- [8] Dorin E. Calbaza and Y. Savaria, "Direct Digital Frequency Synthesis of Low-Jitter Clocks", IEEE Journal of Solid State Circuits, Vol. 36, No. 3, pp. 570-572, March 2001.
- [9] John G. Maneatis, "Low Jitter Process Independent DLL and PLL Based on Self Biased Techniques", IEEE Journal of Solid State Circuit, Vol. 31, No. 11, pp. 1723-1732, Nov. 1996.
- [10] R. E. Best, "Phase-Lock loops, Design, Simulation and Applications", New-York: McGraw-Hill, 1999, 4<sup>rd</sup> Edition.
- [11] E. Roth, M. Thalman, N. Felber, and W. Fichtner, "A Delay-Line Based DCO for Multimedia Application Using Digital Standard Cells", in Dig. Tech. Papers ISSCC'03, Feb. 2003, pp. 432-433.
- [12] J. Dunning, G. Grarcia, J. Lundberg, and Ed Nuckolls, "An All-digital Phase-Locked Loop with 50-cycle Lock Time Suitable for High Performance Microprocessors", IEEE Journal of Solid-state Circuits, Vol. 30, No. 4, pp. 412-422, Apr. 1995.
- [13] K.-J. Lee, H.-C. Kim, U.-R. Cho, H.-G. Byun, and S. Kim, "A Low Jitter ADPLL

- for Mobile Application", IEICE Trans. Electron, Vol-E88-C, No.6, pp. 1241-1247, June 2005.
- [14] C.-C Chung and C.-Y. Lee, "An All Digital Phase-Locked Loop for High-Speed Clock Generation", IEEE Journal of Solid-State Circuits, Vol. 38, No. 2, pp. 347-351, Feb. 2003.
- [15] W. F. Egan, "Phase Lock Basics", John Wiley & Sons, New York, 1998.
- [16] J.-S. Chiang and K.-Y. Chen, "The Design of All Digital Phase Locked Loop with Small DCO Hardware and Fast Phase Lock", IEEE Trans. Circuit and Syst. II, Analog and Digital Signal Processing, Vol. 46, No. 7, pp. 945-950, July 1999.
- [17] H. T. Ahn and D. J. Allstot, "A low-jitter 1.9-V CMOS PLL for ultra-SPARC Microprocessor Applications", IEEE Journal of Solid-State Circuits, Vol. 35, No. 5, pp. 450-454, May 1999.
- [18] Chi-Cheng Cheng, "The Analysis and Design of All-Digital Phase-Locked Loop(ADPLL)," M.S. Dissertation, Department of Electronics Engineering, National Chiao Tung University, Taiwan, July 2001.
- [19] T.Y. Hsu, C.-C. Wang, and C.-Y. Lee "Design and analysis of a portable high-speed clock generator," IEEE Trans. Circuits Syst. II, vol. 48, pp. 367-375, Apr. 2001.
- [20] Thomas Olsson, "A digitally Controlled PLL for SoC Applications", IEEE J. Solid-State Circuits, vol.39, no.5, pp. 751-759, May. 2004.
- [21] Tzu-Chiang Chao and Wei Hwang, "A 1.7mW All Digital Phase Locked Loop with New Gain Generator and Low Power DCO", IEEE ISCAS, pp. 4867-4870, May 2006.
- [22] Amr M. Fahim, "A compact, Low Jitter Digital PLL", in proc. IEEE ESSCIRC'03, 29<sup>th</sup> European Solid State Circuit Conf., Sep. 2003, pp. 101-104.
- [23] I.-O. Hwang, S.-H. Lee and S.-W. Kim, "A Digitally Controlled Phase Locked Loop With a Digital Phase Frequency Detector for Fast Acquisition", IEEE Journal of Solid state Circuits, Vol. 36, No. 10, pp. 1574-1581, Oct. 2001.
- [24] M. Saint-Laurent, and M. Swaminathan, "A Digital Adjustable Resistor for Path Delay Characterization in High-Frequency Microprocessors", IEEE Southwest Symposium on Mixed-Signal Design, 2001.
- [25] Pao-Lung Chen, Ching-Che Chung, and Chen-Yi Lee" A Portable Digitally Controlled Oscillator Using Novel Varactors", IEEE Transaction on Circuit and Systems, Vol. 52, NO. 5, MAY 2005.
- [26] G.-K. Dehng, J.-W. Lin, and S.-I. Liu, "A Fast-Lock Mixed-Mode DLL using a 2-b SAR Algorithm", IEEE Journal of Solid state Circuits, 36(10):1464-1471, Oct. 2001.
- [27] Chia-Tsun Wu, An-yeu Wu."A Scalable DCO Design for Portable ADPLL

- Designs", IEEE International Symposium on Circuits and Systems, Page(s):5449 5452, May 2005.
- [28] J. Lin, B. Haroun, T. Foo, J.-S. Wang, B. Helmick, S. Randall, T. Mayhungh, C. Barr and J. Kirkpartick, "A PVT Tolerant 0.18MHz to 600 MHz Self-Calibrated Digital PLL in 90nm CMOS Process", IEEE ISSCC'04, pp. 488-489, Feb. 2004.
- [29] P. Raha, S. Randall, R. Jennings, B. Helmick, A. Amerasekera, B. Haroun, "A Robust Digital Delay Line Architecture in A 0.13um CMOS Technology Node for Reduced Design and Process Sensitivities", in Proceedings of ISQED'02, pp. 148-153, March 2002.
- [30] Neil H.E. Weste, David Harris, "CMOS VLSI Design A Circuits and Systems Perspective", Third Edition 2004.
- [31] Kwang-Jin Lee; Seung-Hun Jung; Yun-Jeong Kim; Chul Kim; Suki Kim; Uk-Rae Cho; Choong-Guen Kwak; Hyun-Geun Byun; "A Digitally Controlled Oscillator for Low Jitter All Digital Phase Locked Loops" Asian Solid-State Circuits Conference, Page(s):365 368, Nov. 2005.
- [32] M. Maymandi-Nejad and M. Sachdev,"A montonic digitally controlled delay element", *IEEE J. Solid-State Circuits*, vol.40,no.11,pp.2212-2219,Nov. 2005.
- [33] Sheng D., Chung C.-C., Lee C.-Y., "An Ultra-Low-Power and Portable Digitally Controlled Oscillator for SoC Applications", IEEE Transaction on Circuit and Systems-II, 2007.